



**ALPHA & OMEGA**  
SEMICONDUCTOR

## ***AOS Semiconductor Product Reliability Report***

**AO4409 / AO4409L, rev B**

**Plastic Encapsulated Device**

**ALPHA & OMEGA Semiconductor, Inc**

**495 Mercury Drive  
Sunnyvale, CA 94085  
U.S.**

**Tel: (408) 830-9742**

**[www.aosmd.com](http://www.aosmd.com)**

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This AOS product reliability report summarizes the qualification result for AO4409. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AO4409 passes AOS quality and reliability requirements. The released product will be categorized by the process family and be monitored on a quarterly basis for continuously improving the product quality.

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### I. Product Description:

AO4409 / AO4409L, a p channel MOSFET, is mostly used as a bi-directional load switch for battery protection. The device stays in the ON-state during battery charging & discharging most of the time. It is in OFF state only under over-charge / over-discharge conditions. The device transition slowly between on and off states. AO4409 uses advance sub-micron technology on wafer manufacturing.

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted				
Parameter		Symbol	Maximum	Units
Drain-Source Voltage		$V_{DS}$	-30	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>A</sup>	$T_A=25^\circ\text{C}$	$I_D$	-15	A
	$T_A=70^\circ\text{C}$		-12.8	
Pulsed Drain Current <sup>B</sup>		$I_{DM}$	-80	
Power Dissipation <sup>A</sup>	$T_A=25^\circ\text{C}$	$P_D$	3	W
	$T_A=70^\circ\text{C}$		2.1	
Junction and Storage Temperature Range		$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

Thermal Characteristics					
Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient	$t \leq 10\text{s}$	$R_{\theta JA}$	26	40	$^\circ\text{C/W}$
	Steady-State		50	75	$^\circ\text{C/W}$
Maximum Junction-to-Lead		$R_{\theta JL}$	14	24	$^\circ\text{C/W}$

## II. Die / Package Information:

	<b>AO4409</b>	<b>AO4409L (Green Compound)</b>
<b>Process</b>	Standard sub-micron low voltage P channel process	Standard sub-micron low voltage P channel process
<b>Package Type</b>	8 lead SO	8 lead SO
<b>Lead Frame</b>	Copper with Solder Plate	Copper with Solder Plate
<b>Die Attach</b>	Silver-filled Epoxy	Silver-filled Epoxy
<b>Bondwire</b>	2 mils Au wire	2 mils Au wire
<b>Mold Material</b>	Epoxy resin with silica filler	Epoxy resin with silica filler
<b>Filler % (Spherical/Flake)</b>	50/50	100/0
<b>Flammability Rating</b>	UL-94 V-0	UL-94 V-0
<b>Backside Metallization</b>	Ti / N / Ag	Ti / N / Ag
<b>Moisture Level</b>	Up to Level 1 *	Up to Level 1*

**Note \*** based on info provided by assembler and mold compound supplier

## III. Result of Reliability Stress for AO4409 (Standard) & AO4409L (Green)

Test Item	Test Condition	Time Point	Lot Attribution	Total Sample size	Number of Failures
<b>HTGB</b>	Temp = 150 C, Vgs=100% of Vgsmax	168 / 500 hrs  1000 hrs	AO4409: 4 lots <b>AO4409L: 1 lot</b>  (note A*)	410 pcs  77+5 pcs / lot	0
<b>HTRB</b>	Temp = 150 C, Vds=80% of Vdsmax	168 / 500 hrs  1000 hrs	AO4409: 4 lots <b>AO4409L: 1 lot</b>  (note A*)	410 pcs  77+5 pcs / lot	0
<b>HAST</b>	130 +/- 2 C, 85%, 33.3 psi, Vgs = 80% of Vgs max	100 hrs	Standard compound: 3 lots <b>Green compound: 7 lots (note B**)</b>	550 pcs (10 lots)  50+5 pcs / lot	0
<b>Pressure Pot</b>	121 C, 15+/-1 PSIG, RH=100%	96 hrs	Standard compound: 3 lots <b>Green compound: 8 lots ** (note B**)</b>	605 pcs (11 lots)  50+5 pcs / lot	0
<b>Temperature Cycle</b>	-65 to 150 deg C, air to air, 0.5hr per cycle	250 / 500 cycles	Standard compound: 3 lots <b>Green compound: 6 lots ** (note B**)</b>	495 pcs (9 lots)  50+5 pcs / lot	0
<b>ESD Rating</b>	Human Body Mode MIL-STD 883D Method 3025.7	3500V	10 pcs each from AO4409 and AO4409L	20 pcs	0

### III. Result of Reliability Stress for AO4405 (Standard) & AO4405L (Green) Continues

<b>DPA</b>	Internal Vision Cross-section X-ray	NA	5 5 5	5 5 5	0
<b>CSAM</b>		NA	5	5	0
<b>Bond Integrity</b>	Room Temp 150°C bake 150°C bake	0hr 250hr 500hr	40 40 40	40 wires 40 wires 40 wires	0
<b>Solderability</b>	230°C	5 sec	15	15 leads	0
<b>Die shear</b>	150°C	0hr	10	10	0

**Note A:** The HTGB and HTRB reliability data presents total of available AO4409 and AO4409L burn-in data up to the published date.

**Note B:** The pressure pot, temperature cycle and HAST reliability data for **AO4409L** comes from the AOS generic green compound package qualification data.

### IV. Reliability Evaluation

**FIT rate (per billion): 8.64.**

**MTBF=13212 years**

500 hrs of HTGB, 150 deg C accelerated stress testing is equivalent to 15 years of lifetime at 55 deg C operating conditions (by applying the Arrhenius equation with an activation energy of 0.7eV and 60% of upper confidence level on the failure rate calculation). AOS reliability group also routinely monitors the product reliability up to 1000 hr at and performs the necessary failure analysis on the units failed for reliability test(s).

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size of the selected product (AO4409). Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

$$\text{Failure Rate} = \text{Chi}^2 \times 10^9 / [2 (N) (H) (Af)] = 1.83 \times 10^9 / [2 (820) (500) (258.24)] = 8.64$$

$$\text{MTBF} = 10^9 / \text{FIT} = 1.16 \times 10^8 \text{hrs} = 13212 \text{years}$$

**Chi<sup>2</sup>** = Chi Squared Distribution, determined by the number of failures and confidence interval

**N** = Total Number of units from HTRB and HTGB tests

**H** = Duration of HTRB/HTGB testing

**Af** = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse = 55C)

$$\text{Acceleration Factor [Af]} = \text{Exp} [Ea / k ( 1/T] u - 1/T] s ]]$$

**Acceleration Factor ratio list:**

	55 deg C	70 deg C	85 deg C	100 deg C	115 deg C	130 deg C	150 deg C
<b>Af</b>	<b>258</b>	<b>87</b>	<b>32</b>	<b>13</b>	<b>5.64</b>	<b>2.59</b>	<b>1</b>

**Tj s** = Stressed junction temperature in degree (Kelvin),  $K = C + 273.16$

**Tj u** = The use junction temperature in degree (Kelvin),  $K = C + 273.16$

**k** = Boltzman's constant,  $8.617164 \times 10^{-5} \text{ eV} / \text{K}$

**V. Quality Assurance Information**

Acceptable Quality Level for outgoing inspection: **0.1%** for electrical and visual.

Guaranteed Outgoing Defect Rate: **< 25 ppm**

Quality Sample Plan: conform to **Mil-Std-105D**